Notice of References Cited Application/Control No. O9/974,814 Examiner Tuan Quach Applicant(s)/Patent Under Reexamination SAHARA ET AL. Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-		-	
	В	US-			
	C	US-			
	D	US-			
	Е	US-			
	F	US-			
	G	US-			
	Н	US-			
	l	US-		,	
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	К	US-			10
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	S					
	Т					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	Hong, Q., et al., CoSi2 with Low Diode Leakage , IEDM Tech. Digest, December 1997, pp. 107-110.			
	V	Rho, K., et al., Dependence of Deep Submicron CMOSFET Characteristics , International Conference of Microelectronics and VLSI, November 1995, pp. 291-294.			
	w	Yan, R., et al., High Performance 0.1 um Room Temperature Si MOSFETs, Symposium on VLSI Digest of Technical Papers, 1995, pp. 86-87.			
	×	Lee, S., et al., A High Performance 0.13 um CMOS Process, IEEE 6th International Conference of VLSI and CAD, October 1999, pp. 136-139.			

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.